

**BD896 – BD898 – BD900 – BD902**
**SILICON DARLINGTON POWER TRANSISTORS**

PNP epitaxial-base transistors in a monolithic Darlington circuit and housed in a TO-220 envelope. They are intended for use in output stages in audio equipment, general amplifiers, and analogue switching application.

NPN complements are BD895 - BD897 - BD899 - BD901

Compliance to RoHS.

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Ratings	Value	Unit	
$V_{CBO}$	Collector-Base Voltage	BD896	-45	V
		BD898	-60	
		BD900	-80	
		BD902	-100	
$V_{CEO}$	Collector-Emitter Voltage	BD896	-45	V
		BD898	-60	
		BD900	-80	
		BD902	-100	
$V_{EBO}$	Emitter-Base Voltage	BD896	-5	V
		BD898		
		BD900		
		BD902		
$I_C$	Collector Current	BD896	-8	A
		BD898		
		BD900		
		BD902		
$I_B$	Base Current	BD896	-300	mA
		BD898		
		BD900		
		BD902		
$P_T$	Power Dissipation	$T_c = 25^\circ$	70	Watts
		$T_a = 25^\circ$	2	
$T_J$	Junction Temperature	150	°C	
$T_s$	Storage Temperature range	-65 to +150		

**BD896 – BD898 – BD900 – BD902**
**ELECTRICAL CHARACTERISTICS**

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit					
$I_{CBO}$	Collector Cutoff Current	$I_E = 0$ $V_{CB} = -45\text{ V}$	$T_C = 25^\circ\text{C}$	BD896	-	-	-0.2	mA				
		$I_E = 0$ $V_{CB} = -60\text{ V}$		BD898								
		$I_E = 0$ $V_{CB} = -80\text{ V}$		BD900								
		$I_E = 0$ $V_{CB} = -100\text{ V}$		BD902								
		$I_E = 0$ $V_{CB} = -45\text{ V}$	$T_C = 100^\circ\text{C}$	BD896					-	-	-2	mA
		$I_E = 0$ $V_{CB} = -60\text{ V}$		BD898								
		$I_E = 0$ $V_{CB} = -80\text{ V}$		BD900								
		$I_E = 0$ $V_{CB} = -100\text{ V}$		BD902								
$I_{CEO}$	Collector Cutoff Current	$I_E = 0, V_{CE} = -30\text{ V}$	BD896	-	-	-0.5	mA					
		$I_E = 0, V_{CE} = -30\text{ V}$	BD898									
		$I_E = 0, V_{CE} = -40\text{ V}$	BD900									
		$I_E = 0, V_{CE} = -50\text{ V}$	BD902									
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{ V}, I_C = 0$	BD896	-	-	-2	mA					
			BD898									
			BD900									
			BD902									
$V_{CEO}$	Collector-Emitter Breakdown Voltage (*)	$I_C = -100\text{ mA}, I_B = 0$	BD896	-45	-	-	V					
			BD898	-60	-	-						
			BD900	-80	-	-						
			BD902	-100	-	-						
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -3\text{ A}, I_B = -12\text{ mA}$	BD896	-	-	-2.5	V					
			BD898									
			BD900									
			BD902									

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### ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings			Min	Typ	Max	Unit
$V_{BE(on)}$	Base-Emitter Voltage (*)	$I_C = -3\text{ A}, V_{CE} = -3\text{ V}$	BD896	-	-	-2.5	V
			BD898				
			BD900				
			BD902				
$h_{FE}$	DC Current Gain (*)	$V_{CE} = -3.0\text{ V}$ $I_C = -3\text{ A}$	BD896	750	-	-	-
			BD898				
			BD900				
			BD902				
$V_{ECF}$	C-E Diode Forward Voltage	$I_E = -8\text{ A}$	BD896	-	-	-3.5	V
			BD898				
			BD900				
			BD902				

### SWITCHING TIMES

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$t_{on}$	turn-on time	$I_C = -3\text{ A}, V_{BE(off)} = 3.5\text{ V}$ $I_{Bon} = -I_{Boff} = -12\text{ mA}, R_L = 10\ \Omega$	-	1	-	$\mu\text{s}$
$t_{off}$	turn-off time		-	5	-	

(\*) Pulse Width  $\approx 300\ \mu\text{s}$ , Duty Cycle  $\angle 2.0\%$

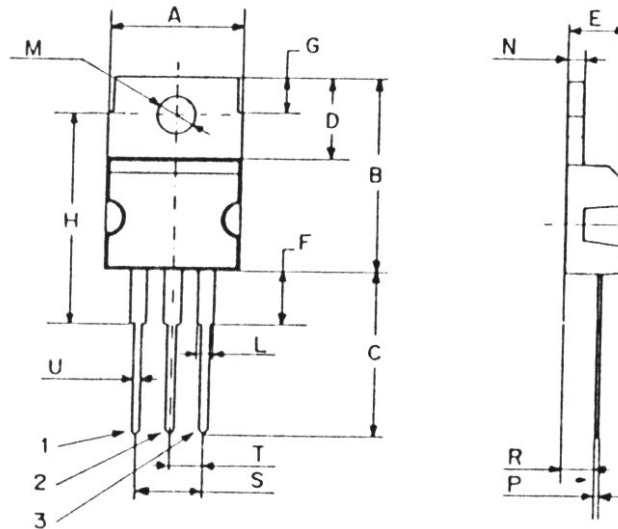
### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{thJ-C}$	Thermal Resistance Junction To Case	1.79	$^{\circ}\text{C/W}$
$R_{thJ-A}$	Thermal Resistance Junction To Free Air	62.5	$^{\circ}\text{C/W}$

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**MECHANICAL DATA CASE TO-220**

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

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